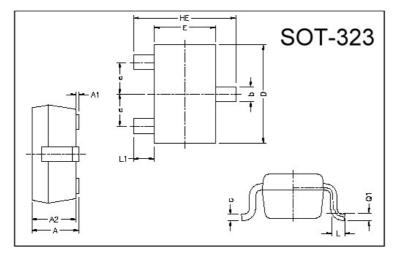
GS401SD

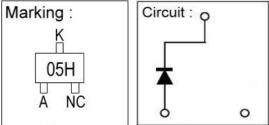
SURFACE MOUNT, SCHOTTKY BARRIER DIODE **VOLTAGE 30V, CURRENT 0.2A**

Description

The GS401SD is high frequency rectification for switching power supply.

Package Dimensions





REF.	Millimeter		REF.	Millimeter					
	Min.	Max.	nLI.	Min.	Max.				
Α	0.80	1.10	L1	0.42 REF.					
A1	0	0.10	L	0.15	0.35				
A2	0.80	1.00	b	0.25	0.40				
D	1.80	2.20	С	0.10	0.25				
Е	1.15	1.35	е	0.65 REF.					
HE	1.80	2.40	Q1	0.15 BSC.					

Absolute Maximum Ratings at TA = 25° C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	$^{\circ}\mathbb{C}$
Storage Temperature	Tstg	-55 ~ +125	$^{\circ}\mathbb{C}$
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	30	V
Maximum RMS Voltage	V_{RMS}	21	V
Maximum DC Blocking Voltage	V _{DC}	30	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	А
Typical Junction Capacitance between Terminal (Note 1)	CJ	40	pF
Maximum Average Forward Rectified Current	lo	0.2	Α
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

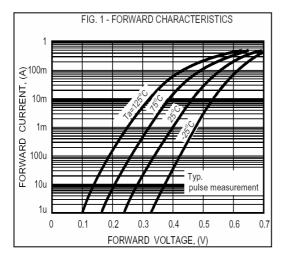
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions			
Reverse Breakdown Voltage	V(BR)R	30	-	-	٧	IR=100μA			
Maximum Instantaneous Forward Voltage	VF	-	-	500	mV	IF=200mA			
Maximum Average Reverse Current	lR	-	-	50	μΑ	VR1=10V			
iwaximum Average neverse Current		-	-	100	μA	VR2=30V			

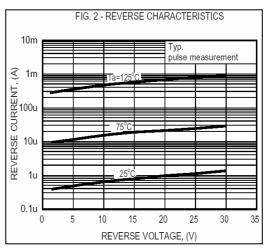
Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

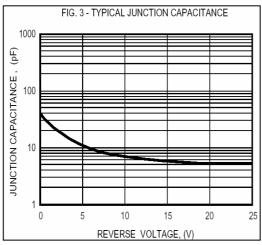
2. ESD sensitive product handling required.

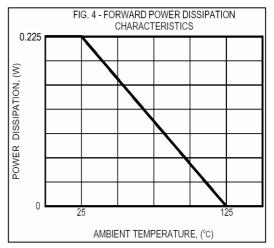
GS401SD Page: 1/2

Characteristics Curve









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GS401SD Page: 2/2